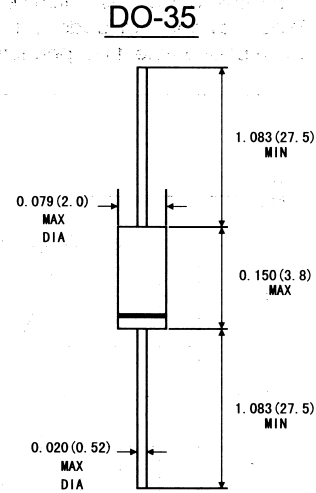


FEATURES

- The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

- Case:** DO-35 glass case
- Polarity:** Color band denotes cathode end
- Weight:** Approx. 0.13gram



Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25°C)

| | Symbols | Value | Units |
|---|------------------|-------------------|-------|
| Zener current see table "Characteristics" | | | |
| Power dissipation at TA=50°C | P _{tot} | 500 ¹⁾ | mW |
| Junction temperature | T _J | 175 | °C |
| Storage temperature range | T _{STG} | -65 to + 175 | °C |

1)Valid provided that at a distance of 8mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS(TA=25°C)

| | Symbols | Min. | Typ. | Max. | Units |
|--|------------------|------|------|-------------------|-------|
| Thermal resistance junction to ambient | R _{θJA} | | | 300 ¹⁾ | K/W |
| Forward voltage at I _F =100mA | V _F | | | 1 | V |

1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature



BXZ55... SILICON PLANAR ZENER DIODES

| Type | Zener Voltage Range ¹⁾ | | | Dynamic resistance | | | Reverse leakage current | | | Temp coefficient of zener voltage |
|-----------------|-----------------------------------|--|-----------|--|------|----|--|------|----|-----------------------------------|
| | V _{ZNOM} | I _{ZT} for V _{ZT} 2) | | r _{zjt} and r _{zjk} at I _{zk} | | | I _R and I _{R2} at V _R | | | TK _{vz} |
| | V | mA | V | Ω | Ω | mA | μA | μA | V | %/K |
| BZX 55/C 0V8 3) | 0.8 | | 0.73.0.83 | <8 | <50 | | - | - | - | -0.26...-0.23 |
| BZX 55/C 2V0 | 2.0 | 5 | 1.9.2.1 | <85 | <600 | 1 | <100 | <200 | <1 | -0.09...-0.06 |
| BZX 55/C 2V4 | 2.4 | | 2.28.2.56 | | | | <50 | <100 | | |
| BZX 55/C 2V7 | 2.7 | | 2.5.2.9 | | | | <10 | <50 | | |
| BZX 55/C 3V0 | 3 | | 2.8.3.2 | | | | <4 | <40 | | |
| BZX 55/C 3V3 | 3.3 | | 3.1.3.5 | | | | <2 | <40 | | |
| BZX 55/C 3V6 | 3.6 | | 3.4.3.8 | | | | <1 | <20 | | |
| BZX 55/C 3V9 | 3.9 | | 3.7.4.1 | | | | <0.5 | <10 | | |
| BZX 55/C 4V3 | 4.3 | | 4.0.4.6 | | | | <75 | | | |
| BZX 55/C 4V7 | 4.7 | | 4.4.5.0 | | | | <60 | | | |
| BZX 55/C 5V1 | 5.1 | | 4.8.5.4 | | | | <35 | <550 | | |
| BZX 55/C 5V6 | 5.6 | | 5.2.6.0 | <25 | <450 | | | | | |
| BZX 55/C 6V2 | 6.2 | | 5.8.6.6 | <10 | <200 | | | | | |
| BZX 55/C 6V8 | 6.8 | | 6.4.7.2 | <8 | <150 | | | | | |
| BZX 55/C 7V5 | 7.5 | | 7.0.7.9 | <7 | <50 | | | | | |
| BZX 55/C 8V2 | 8.2 | | 7.7.8.7 | <7 | | | | | | |
| BZX 55/C 9V1 | 9.1 | | 8.5.9.6 | <10 | | | | | | |
| BZX 55/C 10 | 10 | | 9.4.10.6 | <15 | <70 | | | | | |
| BZX 55/C 11 | 11 | | 10.4.11.6 | <20 | <70 | | | | | |
| BZX 55/C 12 | 12 | | 11.4.12.7 | <20 | <90 | | | | | |
| BZX 55/C 13 | 13 | 12.4.14.1 | <26 | <110 | | | | | | |
| BZX 55/C 15 | 15 | 13.8.15.6 | <30 | <110 | | | | | | |
| BZX 55/C 16 | 16 | 15.3.17.1 | <40 | <170 | | | | | | |
| BZX 55/C 18 | 18 | 16.8.19.1 | <50 | <170 | | | | | | |
| BZX 55/C 20 | 20 | 18.8.21.2 | <55 | <220 | | | | | | |



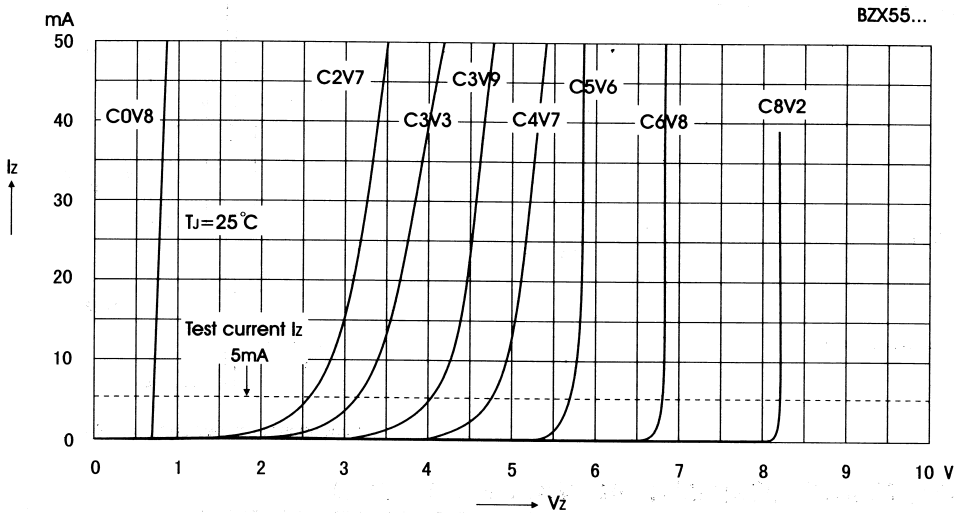
BZX55... SILICON PLANAR ZENER DIODES

| | | | | | | | | | |
|--------------|-----|---------|-----------|--------|------|------|-------|-----|-----------|
| BZX 55/C 22 | 22 | 5 | 20.8.23.3 | <55 | <220 | 1 | <2 | 16 | 0.04.0.12 |
| BZX 55/C 24 | 24 | | 22.8.25.6 | <80 | | | | 18 | |
| BZX 55/C 27 | 27 | | 25.1.28.9 | <80 | | | | 20 | |
| BZX 55/C 30 | 30 | | 28.32 | | | | | 22 | |
| BZX 55/C 33 | 33 | | 31.35 | | | | | 24 | |
| BZX 55/C 36 | 36 | | 34.38 | | | | | 27 | |
| BZX 55/C 39 | 39 | 2.5 | 37.41 | <500 | 0.5 | <0.1 | <5 | 30 | |
| BZX 55/C 43 | 43 | | 40.46 | <500 | | | 33 | | |
| BZX 55/C 47 | 47 | | 44.50 | <600 | | | 36 | | |
| BZX 55/C 51 | 51 | | 48.54 | <700 | | | 39 | | |
| BZX 55/C 56 | 56 | | 52.60 | <700 | | | 43 | | |
| BZX 55/C 62 | 62 | | 58.66 | <1000 | | | 47 | | |
| BZX 55/C 68 | 68 | | 64.72 | | | | 51 | | |
| BZX 55/C 75 | 75 | | 70.79 | | | | 56 | | |
| BZX 55/C 82 | 82 | | 77.87 | | | | <1500 | 62 | |
| BZX 55/C 91 | 91 | | 1 | 85.96 | | | <2000 | 0.1 | |
| BZX 55/C 100 | 100 | 94.106 | | <5000 | 75 | | | | |
| BZX 55/C 110 | 110 | 104.116 | | <5000 | 82 | | | | |
| BZX 55/C 120 | 120 | 114.127 | | <5500 | 91 | | | | |
| BZX 55/C 130 | 130 | 124.141 | | <6000 | 100 | | | | |
| BZX 55/C 150 | 150 | 138.156 | | <6500 | 110 | | | | |
| BZX 55/C 160 | 160 | 153.171 | | <7000 | 120 | | | | |
| BZX 55/C 180 | 180 | 168.191 | | <8500 | 130 | | | | |
| BZX 55/C 200 | 200 | 188.212 | | <10000 | 150 | | | | |

1) Tested with pulses $t_p=20ms$

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.

BZX55... SILICON PLANAR ZENER DIODES**BREAKDOWN CHARACTERISTICS AT T_J =CONSTANT(PULSED)****BREAKDOWN CHARACTERISTICS AT T_J =CONSTANT(PULSED)**